

In the Claims

1. (Currently Amended) An organic electroluminescent device comprising:
a substrate;
a thin film transistor formed on the substrate;
a first electrode electrically coupled to the thin film transistor ~~formed on the substrate;~~
a chemical vapor deposition CVD insulating film having ~~of~~ a low dielectric constant
formed on the first electrode and the substrate, the chemical vapor deposition CVD film having
an opening portion for exposing the first electrode;
an organic electroluminescent (~~EL~~) layer formed on a base and a sidewall of the opening
portion without filling the opening; and
a second electrode formed on the organic electroluminescent EL ~~EL~~ layer.
2. (Currently Amended) The device as claimed in claim 1, wherein the chemical
vapor deposition CVD insulating film comprises ~~is comprised of~~ SiOC.
3. (Currently Amended) The device as claimed in claim 1, wherein the chemical
vapor deposition CVD insulating film has a dielectric constant less than about 3.5.
4. (Currently Amended) The device as claimed in claim 1, wherein the chemical
vapor deposition CVD insulating film is formed to have a thickness more than about 1 μm .
5. (Currently Amended) ~~An~~ The organic electroluminescent device comprising:
a substrate;
a thin film transistor formed on the substrate and having ~~an active pattern;~~ a gate
insulating film, a gate electrode, and source/drain electrodes;
a passivation layer formed on the thin film transistor and the substrate;
a pixel electrode formed on the passivation layer so as to be connected with the thin film
transistor;
a chemical vapor deposition CVD insulating film having ~~of~~ a low dielectric constant

formed on the pixel electrode and the passivation layer, the chemical vapor deposition CVD insulating film having an opening portion for exposing the pixel electrode;

an organic electroluminescent EL layer formed on a base and a sidewall of the opening portion without filling the opening portion; and

a metal electrode formed on the organic electroluminescent EL layer and the chemical vapor deposition CVD insulating film having ~~of~~ a low dielectric constant.

6. (Currently Amended) The device as claimed in claim 5, wherein the chemical vapor deposition CVD insulating film comprises ~~is comprised of~~ SiOC.

7. (Currently Amended) The device as claimed in claim 5, wherein the chemical vapor deposition CVD insulating film has a dielectric constant less than about 3.5.

8. (Currently Amended) The device as claimed in claim 5, wherein the chemical vapor deposition CVD insulating film has a thickness more than about 1 μm .

9. (Currently Amended) The device as claimed in claim 5, wherein the chemical vapor deposition CVD insulating film and an edge portion of the pixel electrode overlap each ~~other in a width~~ by more than about 1 μm .

10. (Currently Amended) An organic electroluminescent device comprising:
a substrate;
a thin film transistor formed on the substrate;
a stripe-shaped first electrode electrically coupled to the thin film transistor ~~formed on the substrate~~;
a chemical vapor deposition CVD insulating film having a ~~of~~ low dielectric constant formed on the first electrode and the substrate, the chemical vapor deposition CVD insulating film having an opening portion formed on the first electrode with a tapered shape;
an organic electroluminescent (~~EL~~) layer formed on the opening portion; and
a stripe-shaped second electrode formed on the organic electroluminescent EL layer, the stripe-shaped second electrode being arranged to cross the first electrode.

11. (Currently Amended) The device as claimed in claim 10, wherein the chemical vapor deposition ~~CVD~~ insulating film is comprised of SiOC.

12. (Currently Amended) The device as claimed in claim 10, wherein the chemical vapor deposition ~~CVD~~ insulating film has a dielectric constant less than about 3.5.

13. (Currently Amended) The device as claimed in claim 10, wherein the chemical vapor deposition ~~CVD~~ insulating film has a thickness more than about 1 μm .